AMENDMENTS TO THE CLAIMS

 (Currently Amended) An SPST (single-pole single-throw) switch for controlling propagation of a high frequency signal between an input terminal and an output terminal, said SPST switch comprising:

a plurality of field-effect transistor (FET) switches, each of said plurality of FET switches is connected in parallel with each other, and each of said plurality of FET switches having a field-effect transistor whose drain and source are directly connected in parallel with an inductor, wherein

the input of said plurality of FET switches is directly connected to the input terminal of said SPST switch and the output of said plurality of FET switches is directly connected to the output terminal of said SPST switch;

each of said field-effect transistors has an ON state and an OFF state changed by a voltage applied to a gate of each of said field-effect transistors, and

each of said field-effect transistors has an OFF capacitance that causes parallel resonance with said inductor connected at a frequency of the high frequency signal.

Claims 2-3. (Canceled)

- 4. (Currently Amended) An SPST (single-pole single-throw) switch for controlling propagation of a high frequency signal between an input terminal and an output terminal, said SPST switch comprising:
- a field-effect transistor (FET) switch constructed by directly connecting an inductor in parallel with a series circuit, the series circuit consisting of a capacitor connected in series with a drain or source of FET, wherein if the drain of the FET is directly connected with the capacitor, then the source of the FET is connected with the input terminal of said SPST switch and if the source of the FET is directly connected with the capacitor, then the drain of the FET is connected with the input terminal of said SPST switch; and wherein

said FET has an ON state and an OFF state changed by a voltage applied to a gate of said FET, and

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said FET has a parasitic inductor and said capacitor that cause series resonance, and has an OFF-capacitance which causes parallel resonance with said inductor causing series resonance with parasitic inductance of the FET, and the inductor causing parallel resonance with parasitic capacitance of the FET and the capacitor.

- 5. (Previously Presented) The SPST switch according to claim 4, wherein the input of said FET switch is directly connected to the input terminal of said SPST switch and the output of said FET switch is directly connected to the output terminal of said SPST switch.
- 6. (Currently Amended) The SPST switch according to claim 5, further comprising a plurality of FET switches, each of said plurality of FET switches is connected in parallel with each other between the input terminal and the output terminal.
 - 7. (Previously Presented) The SPST switch according to claim 4, wherein

the input of said FET switch is directly connected to the input terminal or the output terminal of said SPST; and

the output of said FET switch is directly connected to ground.

- 8. (Currently Amended) The SPST switch according to claim 7, further comprising a plurality of FET switches, each of said plurality of FET switches is connected in parallel with each other, wherein the input of said plurality of parallel FET switches is directly connected to the input terminal of said SPST and the output of said plurality of parallel FET switches is directly connected to ground.
- (Currently Amended) An SPDT (single-pole double-throw) switch for controlling propagation of a high frequency signal between an input terminal and two output terminals, said SPDT switch employing:
- a plurality of field-effect transistor (FET) switches, each of said plurality of FET switches is connected in parallel with each other, and each of said plurality of FET switches having a

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field-effect transistor whose drain and source are directly connected in parallel with an inductor; and

wherein the input of said plurality of parallel FET switches is directly connected to the input terminal of said SPDT switch and the output of said plurality of parallel FET switches is directly connected to a first output terminal of said SPST switch.

10. (Previously Presented) The SPDT switch of claim 9, further comprising:

a single field-effect transistor (FET) switch having an inductor directly connected in parallel with a series circuit, the series circuit consisting of a capacitor connected in series with a drain or source of a field-effect transistor; and

wherein the input of said single FET switch is directly connected to a second output terminal of said SPST switch and the output of said single FET switch is directly connected to ground.

11. (Currently Amended) An MPMT (multiple-pole multiple throw) switch for controlling propagation of a high frequency signal between a plurality of input terminals and a plurality of output terminals, said MPMT switch employing:

a plurality of field-effect transistor (FET) switches connected in parallel, each of said plurality of parallel FET switches having a field-effect transistor whose drain and source are directly connected in parallel with an inductor; and

wherein the input of said plurality of parallel FET switches is directly connected to an input terminal of said MPPT_MPMT switch and the output of said plurality of parallel FET switches is directly connected to an output terminal of said SPST-MPMT switch.

12. (Currently Amended) An MPMT (multiple-pole multiple throw) switch for controlling propagation of a high frequency signal between a plurality of input terminals and a plurality of output terminals, said MPMT switch employing:

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a plurality of field-effect transistor (FET) switches, each of said FET switches having an inductor directly connected in parallel with a series circuit, the series circuit consisting of a capacitor connected in series with a drain or source of a field-effect transistor, and

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wherein said FET switches having their first terminals connected to corresponding input terminal or output terminal of the said MPMT switch and wherein said FET switches having their second terminals connected with each other.

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